**11 February 2015** 

**Product data sheet** 

## 1. General description

NPN/NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020D-6 (SOT1118D) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN/PNP complement: PBSS4160PANPS. PNP/PNP complement: PBSS5160PAPS.

## 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- Reduced Printed-Circuit Board (PCB) requirements
- Exposed heat sink for excellent thermal and electrical conductivity
- High energy efficiency due to less heat generation
- Suitable for Automatic Optical Inspection (AOI) of solder joints
- AEC-Q101 qualified

## 3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- LED lighting
- Power switches (e.g. motors, fans)

#### 4. Quick reference data

Table 1. Quick reference data

| Symbol           | Parameter                 | Conditions                          |  | Min | Тур | Max | Unit |
|------------------|---------------------------|-------------------------------------|--|-----|-----|-----|------|
| Per transistor   | Per transistor            |                                     |  |     |     |     |      |
| V <sub>CEO</sub> | collector-emitter voltage | open base                           |  | -   | -   | 60  | V    |
| I <sub>C</sub>   | collector current         |                                     |  | -   | -   | 1   | Α    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |  | -   | -   | 1.5 | Α    |



| Symbol             | Parameter                               | Conditions   | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-----|-----|------|
| Per transistor     |   |  |     |     |     |      |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_C$ = 0.5 A; $I_B$ = 50 mA; pulsed;<br>$t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C | -   | -   | 240 | mΩ   |

# 5. Pinning information

**Table 2.** Pinning information

| 10010 21 |        |               |   |                |
|----------|--------|---------------|---|----------------|
| Pin      | Symbol | Description   | Simplified outline                          | Graphic symbol |
| 1        | E1     | emitter TR1   | 6 5 4                                       | C1 B2 E2       |
| 2        | B1     | base TR1      |   |                |
| 3        | C2     | collector TR2 | 7 8   | (TR1) TR2)     |
| 4        | E2     | emitter TR2   |   |                |
| 5        | B2     | base TR2      | 1 2 3                                       | E1 B1 C2       |
| 6        | C1     | collector TR1 | Transparent top view  DFN2020D-6 (SOT1118D) | sym140         |
| 7        | C1     | collector TR1 | DEN2020D-0 (3011110D)                       |                |
| 8        | C2     | collector TR2 |   |                |

# 6. Ordering information

Table 3. Ordering information

| Type number  | Package    |   |          |  |  |  |
|--------------|------------|---|----------|--|--|--|
|              | Name       | Description   | Version  |  |  |  |
| PBSS4160PANS | DFN2020D-6 | DFN2020D-6: plastic, thermally enhanced ultra thin and small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm | SOT1118D |  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number  | Marking code |
|--------------|--------------|
| PBSS4160PANS | 3F           |

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

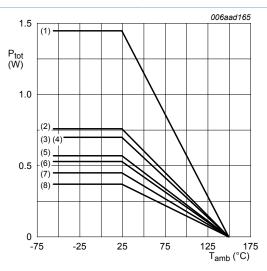
| Symbol           | Parameter                 | Conditions                          |            | Min | Max  | Unit |
|------------------|---------------------------|-------------------------------------|------------|-----|------|------|
| Per transis      | tor                       | '                                   |            |     |      |      |
| $V_{CBO}$        | collector-base voltage    | open emitter                        |            | -   | 60   | V    |
| $V_{CEO}$        | collector-emitter voltage | open base                           |            | -   | 60   | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |            | -   | 7    | V    |
| I <sub>C</sub>   | collector current         |                                     |            | -   | 1    | Α    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |            | -   | 1.5  | Α    |
| I <sub>B</sub>   | base current              |                                     |            | -   | 0.3  | Α    |
| I <sub>BM</sub>  | peak base current         | single pulse; t <sub>p</sub> ≤ 1 ms |            | -   | 1    | Α    |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1]        | -   | 370  | mW   |
|                  |                           |                                     | [2]        | -   | 570  | mW   |
|                  |                           |                                     | [3]        | -   | 530  | mW   |
|                  |                           |                                     | [4]        | -   | 700  | mW   |
|                  |                           |                                     | [5]        | -   | 450  | mW   |
|                  |                           |                                     | [6]        | -   | 760  | mW   |
|                  |                           |                                     | [7]        | -   | 700  | mW   |
|                  |                           |                                     | [8]        | -   | 1450 | mW   |
| Per device       |                           |                                     |            |     |      |      |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1]        | -   | 510  | mW   |
|                  |                           |                                     | [2]        | -   | 780  | mW   |
|                  |                           |                                     | [3]        | -   | 730  | mW   |
|                  |                           |                                     | [4]        | -   | 960  | mW   |
|                  |                           |                                     | <u>[5]</u> | -   | 620  | mW   |
|                  |                           |                                     | [6]        | -   | 1040 | mW   |
|                  |                           |                                     | [7]        | -   | 960  | mW   |
|                  |                           |                                     | [8]        | -   | 2000 | mW   |
| Tj               | junction temperature      |                                     |            | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |            | -55 | 150  | °C   |
| $T_{stg}$        | storage temperature       |                                     |            | -65 | 150  | °C   |

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.

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- [6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



- (1) 4-layer PCB 70 μm, mounting pad for collector 1 cm<sup>2</sup>
- (2) FR4 PCB 70 μm, mounting pad for collector 1 cm<sup>2</sup>
- (3) 4-layer PCB 70 µm, standard footprint
- (4) 4-layer PCB 35 μm, mounting pad for collector 1 cm<sup>2</sup>
- (5) FR4 PCB 35 μm, mounting pad for collector 1 cm<sup>2</sup>
- (6) 4-layer PCB 35 µm, standard footprint
- (7) FR4 PCB 70 µm, standard footprint
- (8) FR4 PCB 35 µm, standard footprint

Fig. 1. Per transistor: power derating curves

#### 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol   | Parameter          | Conditions  |            | Min | Тур | Max | Unit |
|--|--------------------|-------------|------------|-----|-----|-----|------|
| Per transistor   |                    |             |            |     |     |     |      |
| R <sub>th(j-a)</sub> thermal resistance from junction to ambient | thermal resistance | in free air | [1]        | -   | -   | 338 | K/W  |
|  |                    |             | <u>[2]</u> | -   | -   | 219 | K/W  |
|  | ambient            |             | [3]        | -   | -   | 236 | K/W  |
|  |                    |             |            | [4] | -   | -   | 179  |
|  |                    |             | <u>[5]</u> | -   | -   | 278 | K/W  |
|  |                    |             | [6]        | -   | -   | 164 | K/W  |
|  |                    |             | [7]        | -   | -   | 179 | K/W  |
|  |                    |             | [8]        | -   | -   | 86  | K/W  |

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| Symbol         | Parameter  | Conditions            |     | Min | Тур | Max | Unit |
|----------------|--|-----------------------|-----|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |                       |     | -   | -   | 30  | K/W  |
| Per device     |  |                       |     |     |     |     |      |
| ui(j'a)        | thermal resistance                               | ]<br>1<br>1<br>1<br>1 | [1] | -   | -   | 245 | K/W  |
|                | from junction to                                 |                       | [2] | -   | -   | 160 | K/W  |
|                | ambient  |                       | [3] | -   | -   | 171 | K/W  |
|                |  |                       | [4] | -   | -   | 130 | K/W  |
|                |  |                       | [5] | -   | -   | 202 | K/W  |
|                |  |                       | [6] | -   | -   | 120 | K/W  |
|                |  |                       | [7] | -   | -   | 130 | K/W  |
|                |  |                       | [8] | -   | -   | 63  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

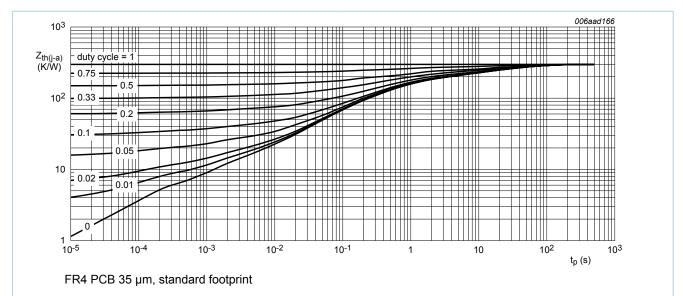


Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

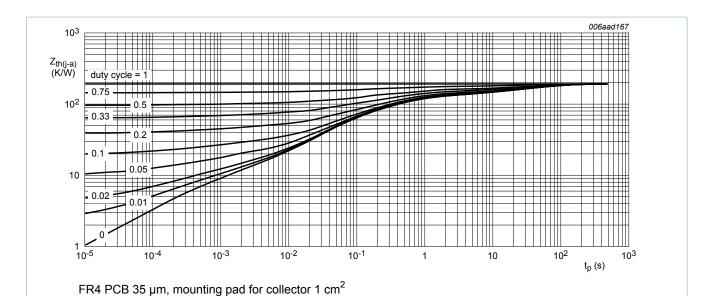


Fig. 3. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

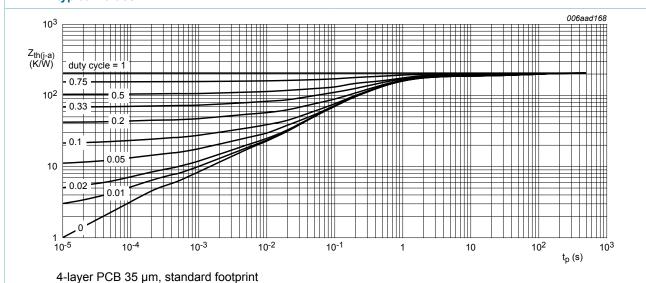


Fig. 4. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

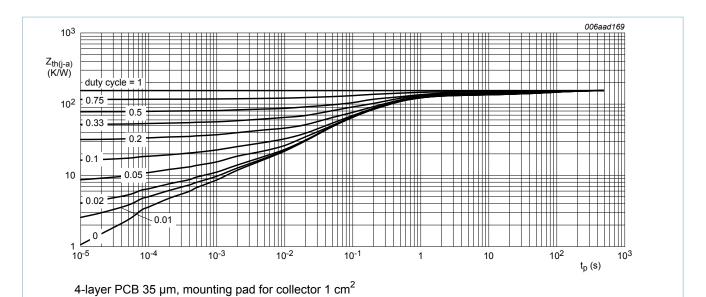


Fig. 5. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

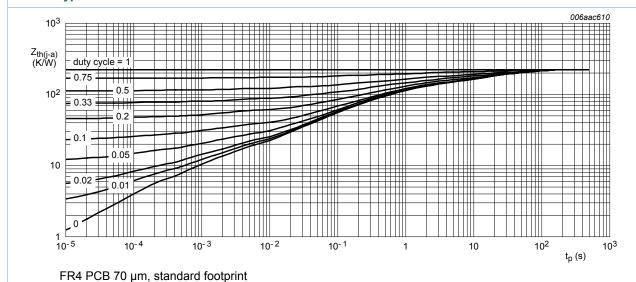
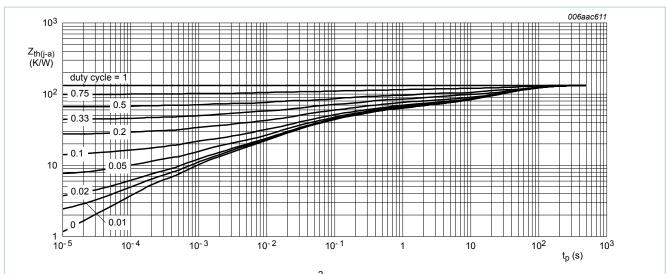
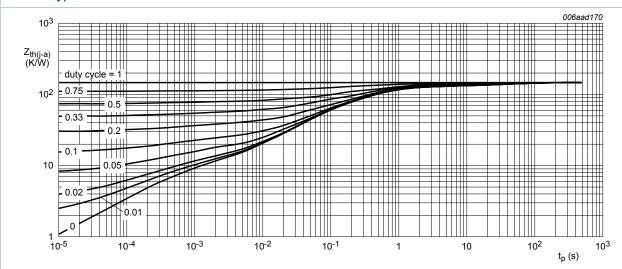


Fig. 6. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB 70 µm, mounting pad for collector 1 cm<sup>2</sup>

Fig. 7. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



4-layer PCB 70 µm, standard footprint

Fig. 8. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

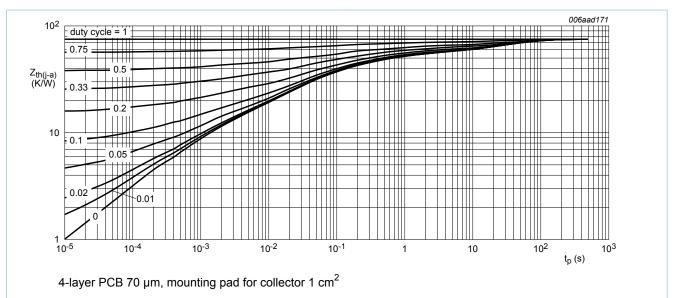


Fig. 9. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10/19

60 V, 1 A NPN/NPN low VCEsat (BISS) transistor

# 10. Characteristics

Table 7. Characteristics

**Product data sheet** 

| Symbol             | Parameter                               | Conditions   | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-----|-----|------|
| Per transis        | tor                                     |  |     |     |     |      |
| I <sub>CBO</sub>   | collector-base cut-off                  | V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C   | -   | -   | 100 | nA   |
|                    | current                                 | V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C  | -   | -   | 50  | μA   |
| I <sub>EBO</sub>   | emitter-base cut-off current            | V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C  | -   | -   | 100 | nA   |
| h <sub>FE</sub>    | DC current gain                         | $V_{CE}$ = 2 V; $I_{C}$ = 100 mA; pulsed;<br>$t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C                                | 290 | 430 | -   |      |
|                    |   | $V_{CE} = 2 \text{ V}; I_{C} = 500 \text{ mA}; \text{ pulsed};$ $t_{p} \le 300 \text{ µs}; \delta \le 0.02; T_{amb} = 25 \text{ °C}$ | 150 | 220 | -   |      |
|                    |   | $V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C                               | 70  | 110 | -   |      |
| V <sub>CEsat</sub> | collector-emitter                       | $I_C$ = 500 mA; $I_B$ = 50 mA; $T_{amb}$ = 25 °C   | -   | 90  | 120 | mV   |
|                    | saturation voltage                      | $I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed;<br>$t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C                           | -   | 185 | 240 | mV   |
|                    |   | $I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed;<br>$t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C                          | -   | 175 | 220 | mV   |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_{C}$ = 0.5 A; $I_{B}$ = 50 mA; pulsed;<br>$t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C                                    | -   | -   | 240 | mΩ   |
| V <sub>BEsat</sub> | base-emitter saturation                 | I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C  | -   | -   | 1   | V    |
|                    | voltage                                 | $I_C$ = 1 A; $I_B$ = 50 mA; pulsed;<br>$t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C                                 | -   | -   | 1.1 | V    |
|                    |   | $I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed;<br>$t_{p} \le 300 \ \mu s$ ; $\overline{o} \le 0.02$ ; $T_{amb}$ = 25 °C                    | -   | -   | 1.1 | V    |
| $V_{BEon}$         | base-emitter turn-on voltage            | $V_{CE} = 2 \text{ V; } I_{C} = 0.5 \text{ A; pulsed;}$<br>$t_{p} \le 300 \text{ µs; } \delta \le 0.02; T_{amb} = 25 \text{ °C}$     | -   | -   | 0.9 | V    |
| t <sub>d</sub>     | delay time                              | V <sub>CC</sub> = 10 V; I <sub>C</sub> = 500 mA; I <sub>Bon</sub> = 25 mA;   | -   | 15  | -   | ns   |
| t <sub>r</sub>     | rise time                               | $I_{Boff}$ = -25 mA; $T_{amb}$ = 25 °C   | -   | 90  | -   | ns   |
| t <sub>on</sub>    | turn-on time                            |  | -   | 105 | -   | ns   |
| t <sub>s</sub>     | storage time                            |  | -   | 410 | -   | ns   |
| t <sub>f</sub>     | fall time                               |  | -   | 130 | -   | ns   |
| t <sub>off</sub>   | turn-off time                           |  | -   | 540 | -   | ns   |
| f <sub>T</sub>     | transition frequency                    | $V_{CE}$ = 10 V; $I_{C}$ = 50 mA; f = 100 MHz;<br>$T_{amb}$ = 25 °C  | 90  | 175 | -   | MHz  |
| C <sub>c</sub>     | collector capacitance                   | $V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A;<br>f = 1 MHz; $T_{amb}$ = 25 °C   | -   | 4   | 6   | pF   |

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9

7.5 6

4.5

3

1.5

### 60 V, 1 A NPN/NPN low VCEsat (BISS) transistor

1.50

1.00

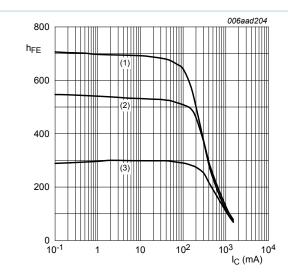
0.75

0.50

0.25

I<sub>C</sub> (A)

 $I_B = 15 \text{ mA}$ 

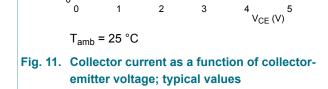


$$V_{CE} = 2 V$$

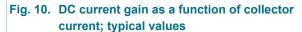
(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

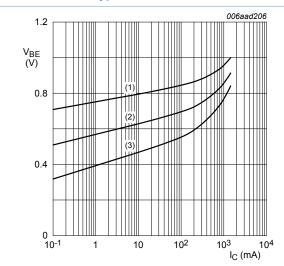
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$



3





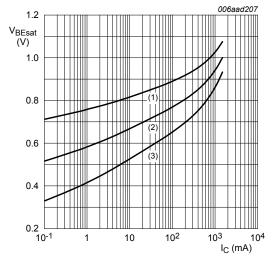
$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = 100 °C$$

Fig. 12. Base-emitter voltage as a function of collector current; typical values



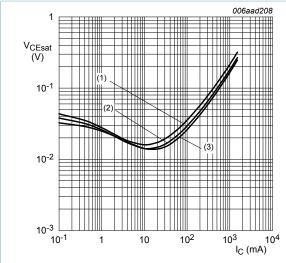
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 13. Base-emitter saturation voltage as a function of collector current; typical values



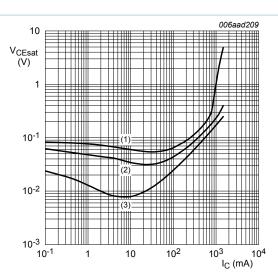
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55$$
 °C

Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values



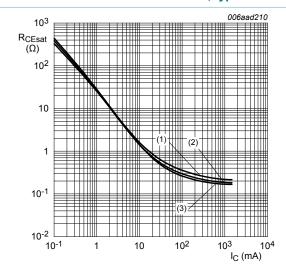
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation voltage as a function of collector current; typical values



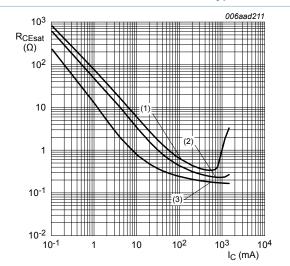
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 16. Collector-emitter saturation resistance as a function of collector current; typical values



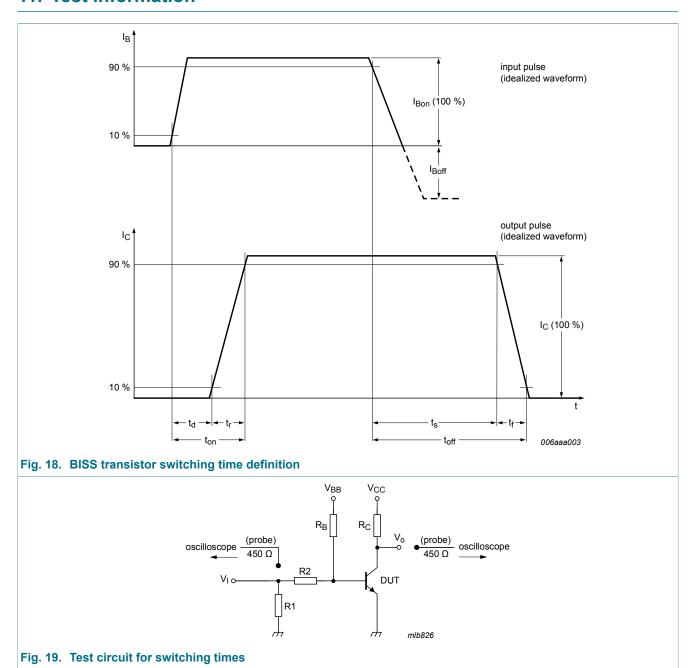
(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 17. Collector-emitter saturation resistance as a function of collector current; typical values

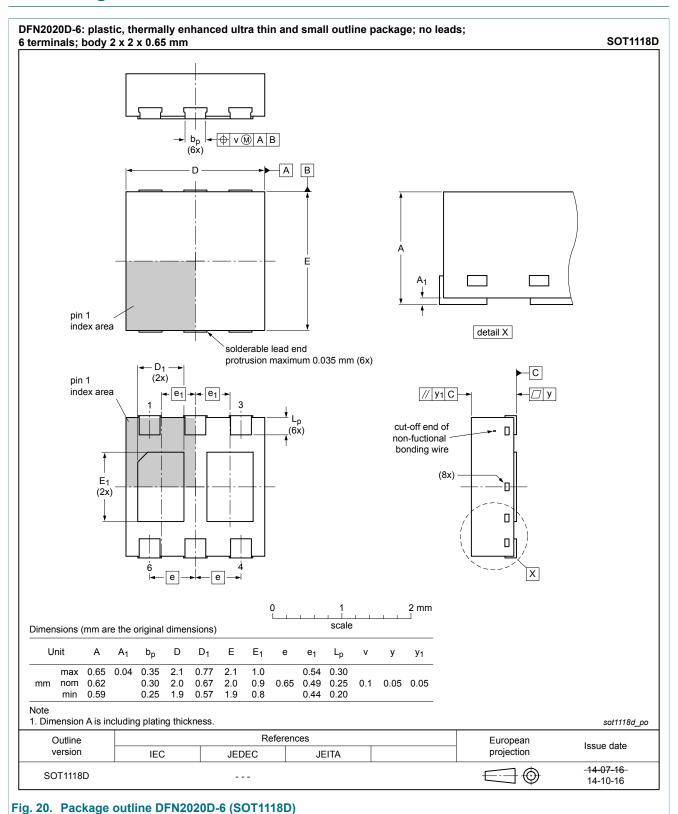
## 11. Test information



## 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline



PBSS4160PANS

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# 13. Soldering

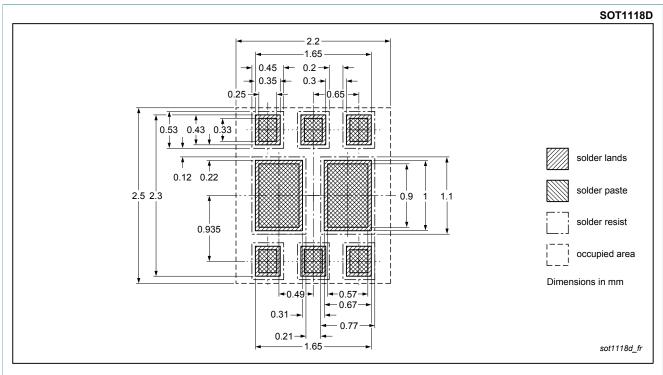


Fig. 21. Reflow soldering footprint for DFN2020D-6 (SOT1118D)

# 14. Revision history

#### Table 8. Revision history

| Data sheet ID    | Release date | Data sheet status  | Change notice | Supersedes |
|------------------|--------------|--------------------|---------------|------------|
| PBSS4160PANS v.1 | 20150211     | Product data sheet | -             | -          |

## 15. Legal information

#### 15.1 Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product<br>[short] data<br>sheet     | Production         | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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#### 15.2 Definitions

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